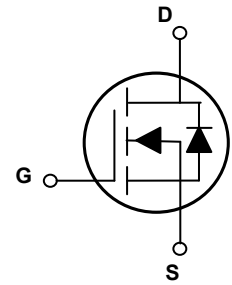
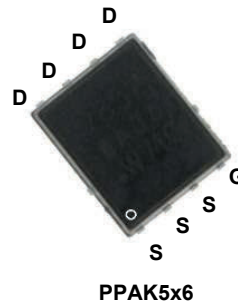


### Main Product Characteristics

|              |                   |
|--------------|-------------------|
| $BV_{DSS}$   | 40V               |
| $R_{DS(ON)}$ | 5m $\Omega$ (Max) |
| $I_D$        | 96A               |



Schematic Diagram

### Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



### Description

The GSFP4005SF utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

| Parameter   | Symbol          | Max.                    | Unit               |   |
|---|-----------------|-------------------------|--------------------|---|
| Drain-Source Voltage                                  | $V_{DS}$        | 40                      | V                  |   |
| Gate-Source Voltage                                   | $V_{GS}$        | $\pm 20$                | V                  |   |
| Drain Current   | $I_D$           | $T_C=25^\circ\text{C}$  | 96                 | A |
|   |                 | $T_C=100^\circ\text{C}$ | 61                 | A |
|   |                 | $T_A=25^\circ\text{C}$  | 27                 | A |
|   |                 | $T_A=70^\circ\text{C}$  | 22                 | A |
| Pulsed Drain Current <sup>2</sup>                     | $I_{DM}$        | 192                     | A                  |   |
| Total Power Dissipation <sup>3</sup>                  | $P_D$           | $T_C=25^\circ\text{C}$  | 78                 | W |
|   |                 | $T_A=25^\circ\text{C}$  | 6.3                | W |
| Thermal Resistance Junction-to-Ambient <sup>1,4</sup> | $R_{\theta JA}$ | 20                      | $^\circ\text{C/W}$ |   |
| Thermal Resistance Junction-to-Case                   | $R_{\theta JC}$ | 1.6                     | $^\circ\text{C/W}$ |   |
| Junction and Storage Temperature Range                | $T_J/T_{STG}$   | -55 to +150             | $^\circ\text{C}$   |   |

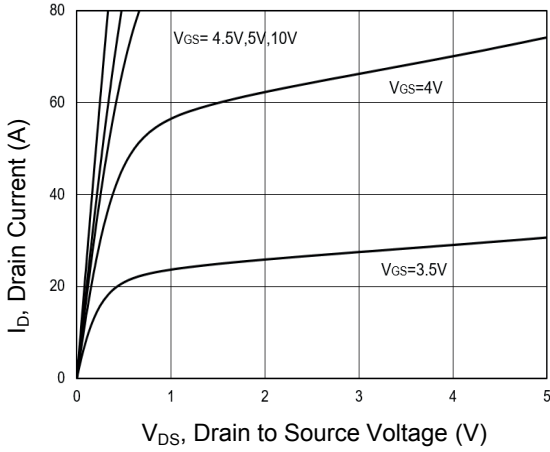
**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

| Parameter                                       | Symbol       | Conditions   | Min | Typ  | Max       | Units      |
|---|--------------|--|-----|------|-----------|------------|
| <b>On / Off Characteristics</b>                 |              |  |     |      |           |            |
| Drain-Source Breakdown Voltage                  | $BV_{DSS}$   | $V_{GS}=0V, I_D=250\mu A$                          | 40  | -    | -         | V          |
| Zero Gate Voltage Drain Current                 | $I_{DSS}$    | $V_{DS}=40V, V_{GS}=0V, T_C=25^{\circ}\text{C}$    | -   | -    | 1         | $\mu A$    |
| Gate-Body Leakage Current                       | $I_{GSS}$    | $V_{GS}=\pm 20V, V_{DS}=0V$                        | -   | -    | $\pm 100$ | nA         |
| Gate Threshold Voltage                          | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$                      | 1.5 | -    | 2.5       | V          |
| Static Drain-Source on-Resistance               | $R_{DS(on)}$ | $V_{GS}=10V, I_D=20A$                              | -   | 4.0  | 5.0       | m $\Omega$ |
|   |              | $V_{GS}=4.5V, I_D=16A$                             | -   | 5.7  | 7.5       |            |
| <b>Dynamic and Switching Characteristics</b>    |              |  |     |      |           |            |
| Input Capacitance                               | $C_{iss}$    | $V_{DS}=20V, V_{GS}=0V, F=1\text{MHz}$             | -   | 4100 | -         | pF         |
| Output Capacitance                              | $C_{oss}$    |  | -   | 280  | -         |            |
| Reverse Transfer Capacitance                    | $C_{rss}$    |  | -   | 275  | -         |            |
| Total Gate Charge                               | $Q_g$        | $V_{GS}=10V, V_{DS}=20V, I_D=20A$                  | -   | 78   | -         | nC         |
| Gate Source Charge                              | $Q_{gs}$     |  | -   | 11.5 | -         |            |
| Gate Drain Charge                               | $Q_{gd}$     |  | -   | 18   | -         |            |
| Turn-on Delay Time                              | $t_{d(on)}$  | $V_{GS}=10V, V_{DD}=20V, I_D=20A, R_{GEN}=3\Omega$ | -   | 27.8 | -         | nS         |
| Turn-on Rise Time                               | $t_r$        |  | -   | 12.8 | -         |            |
| Turn-off Delay Time                             | $t_{d(off)}$ |  | -   | 96   | -         |            |
| Turn-off Fall Time                              | $t_f$        |  | -   | 24   | -         |            |
| <b>Source-Drain Ratings and Characteristics</b> |              |  |     |      |           |            |
| Diode Forward Voltage                           | $V_{SD}$     | $I_S=20A, V_{GS}=0V$                               | -   | 0.8  | 1.2       | V          |
| Maximum Body-Diode Continuous Current           | $I_S$        | -  | -   | -    | 96        | A          |

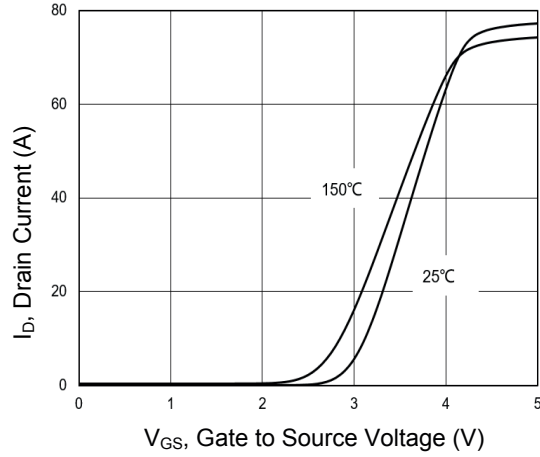
Notes:

1. The value of  $R_{\theta JA}$  is measured with the device mounted on lin2 FR-4 board with 2oz.Copper,in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any given application depends on the user's specific board design.
2. Single pulse width limited by junction temperature  $T_{J(MAX)}=150^{\circ}\text{C}$ .
3. The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
4. The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case and case to ambient.

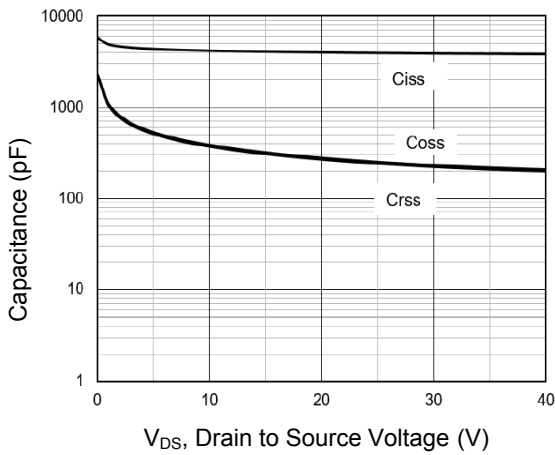
**Typical Electrical and Thermal Characteristic Curves**



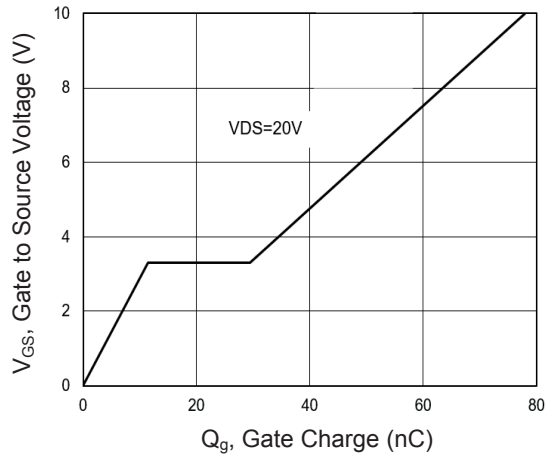
**Figure 1. Output Characteristics**



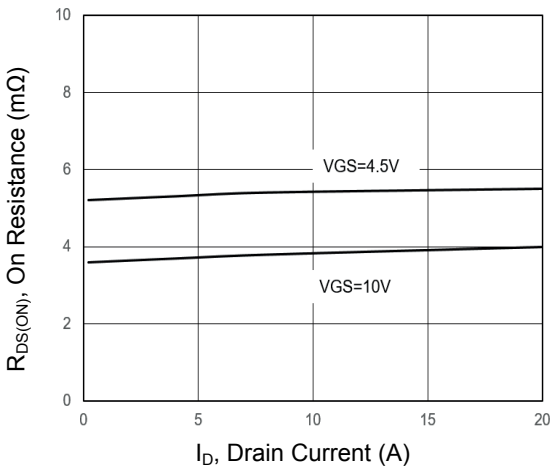
**Figure 2. Transfer Characteristics**



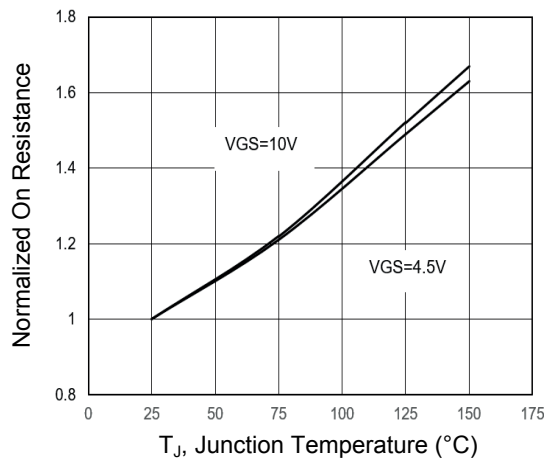
**Figure 3. Capacitance Characteristics**



**Figure 4. Gate Charge**

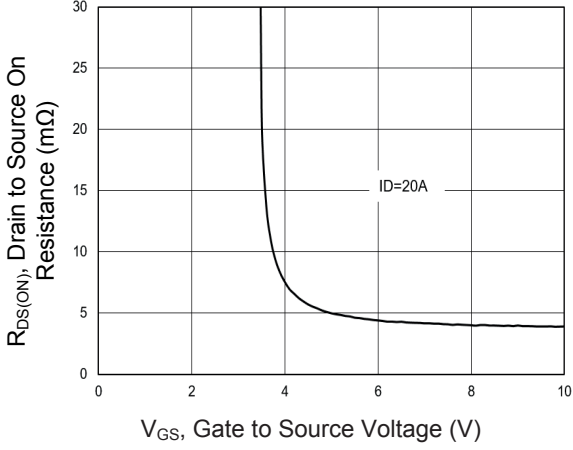


**Figure 5. Drain-Source on Resistance**

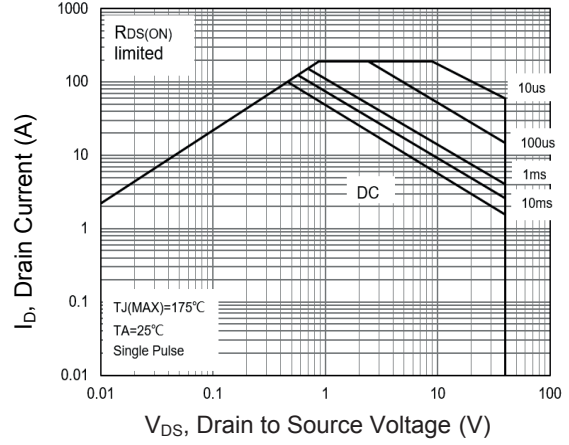


**Figure 6. Normalized  $R_{DS(on)}$  vs.  $T_J$**

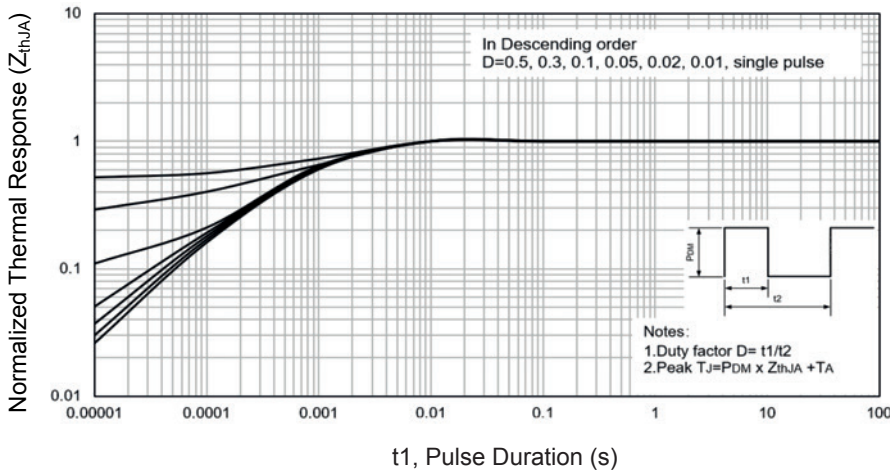
**Typical Electrical and Thermal Characteristic Curves**



**Figure 7. Typical Drain to Source ON Resistance vs. Gate Voltage and Drain Current**

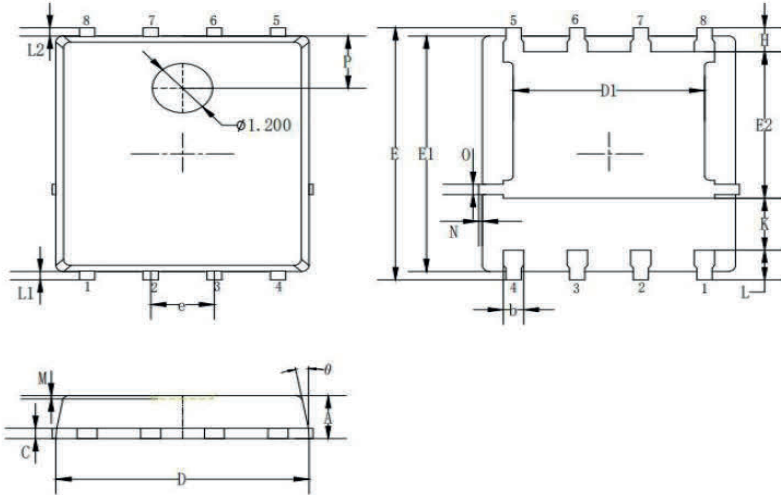


**Figure 8. Safe Operation Area**



**Figure 9. Maximum Effective Transient Thermal Impedance, Junction-to-Case**

**Package Outline Dimensions (PPAK5x6)**



| Symbol | Dimensions In Millimeters |      | Dimensions In Inches |       |
|--------|---------------------------|------|----------------------|-------|
|        | Min.                      | Max. | Min.                 | Max.  |
| A      | 0.90                      | 1.20 | 0.035                | 0.047 |
| b      | 0.35                      | 0.50 | 0.014                | 0.020 |
| c      | 0.20                      | 0.35 | 0.008                | 0.014 |
| D      | 4.90                      | 5.20 | 0.193                | 0.205 |
| D1     | 3.72                      | 3.92 | 0.146                | 0.154 |
| E      | 6.00                      | 6.30 | 0.236                | 0.248 |
| E1     | 5.60                      | 5.90 | 0.220                | 0.232 |
| E2     | 3.47                      | 3.67 | 0.137                | 0.144 |
| e      | 1.27 BSC                  |      | 0.050 BSC            |       |
| H      | 0.48                      | 0.68 | 0.019                | 0.027 |
| K      | 1.17                      | 1.37 | 0.046                | 0.054 |
| L      | 0.64                      | 0.84 | 0.025                | 0.033 |
| L1/L2  | 0.20 REF                  |      | 0.008 REF            |       |
| θ      | 8°                        | 12°  | 8°                   | 12°   |
| M      | 0.08 REF                  |      | 0.003 REF            |       |
| N      | 0                         | 0.15 | 0.000                | 0.006 |
| O      | 0.25 REF                  |      | 0.010 REF            |       |
| P      | 1.28 REF                  |      | 0.050 REF            |       |

**Order Information**

| Device     | Package | Marking  | Carrier     | Quantity        |
|------------|---------|----------|-------------|-----------------|
| GSFP4005SF | PPAK5x6 | N4005SF5 | Tape & Reel | 5,000pcs / Reel |

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